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Accession number:20123515377696

Title:Ultrahigh speed graphene diode with reversible polarity

Authors: Moddel, Garret (1); Zhu, Zixu (1); Grover, Sachit (1); Joshi, Saumil (1)

Author affiliation:(1) Department of Electrical, Computer and Energy Engineering, University of Colorado, Boulder, CO 80309-0425, United States; (2) National Center for Photovoltaics, National Renewable Energy Laboratory, 1617 Cole Blvd., Golden, CO 80401, United States

National Renewable Energy Laboratory, 1017 Cole Brvd., Goldell, CO 80401, United S

 $Corresponding \ author: Moddel, \ G.(moddel@colorado.edu)$

Source title:Solid State Communications

Abbreviated source title:Solid State Commun

Volume:152

Issue:19

Issue date:October 2012

Publication year:2012

Pages:1842-1845

Language:English

ISSN:00381098

CODEN:SSCOA4

Document type:Journal article (JA)

Publisher: Elsevier Ltd, Langford Lane, Kidlington, Oxford, OX5 1GB, United Kingdom

Abstract: The ability to tune the carrier-type concentration ratio with applied field along with a mean-free path length approaching 1 μm in graphene enables a new diode in which the diode polarity can be reversed. The diode consists of a thin graphene film with a geometric asymmetry that determines a preferred direction for charge-carrier transport, independent of whether the carriers are electrons or holes. We fabricated submicron geometric diodes by patterning and etching exfoliated graphene. Applying field-effect voltages to the substrate, we reversed the carrier type and demonstrated reversal of the diode polarity. The graphene geometric diodes exhibited rectification at 28 THz, opening the way to ultrahigh speed applications for these versatile devices. © 2012 Elsevier Ltd.

Number of references:27

Main heading: Diodes

Controlled terms:Geometry - Graphene

Uncontrolled terms:Applied field - Charge-carrier transport - Concentration ratio - Dirac point -Field-effect - Geometric asymmetries - Mean-free path length - Submicron - Tera Hertz - Ultra high speed - Ultra-high speed applications

Classification code:714.2 Semiconductor Devices and Integrated Circuits - 761 Nanotechnology - 804 Chemical Products Generally - 921 Mathematics

DOI:10.1016/j.ssc.2012.06.013

Database:Compendex

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